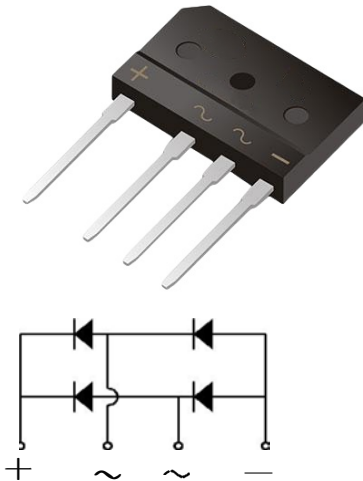


Low VF Bridge Rectifiers



Features

- Glass Passivated Chip Junction
- Low IRRM
- Ultra Low VF
- High VRRM

Benefits

- Case: GBJ
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor
- Reduced snubbing

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	GBJ2506L	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC Blocking Voltage	VDC	600	V
Average Rectified Output Current	I _o	25.0	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	300	A
Maximum Forward Voltage at 12.5 A	VF	0.93	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10 500	μA
Typical Junction Capacitance (Note1)	Cj	25	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C
Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.			

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

Fig.1 Current Derating, Case

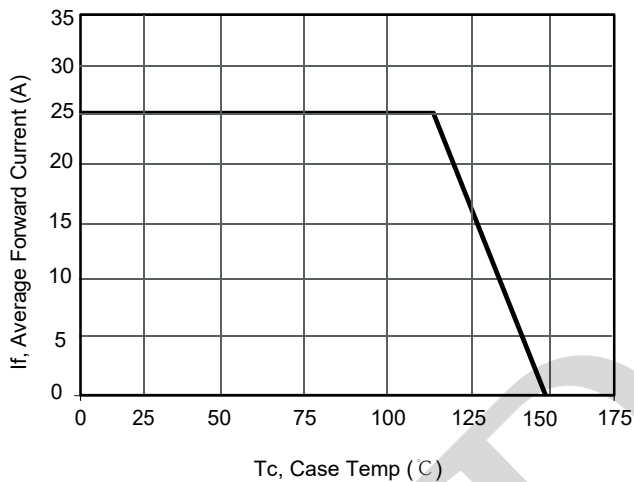


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

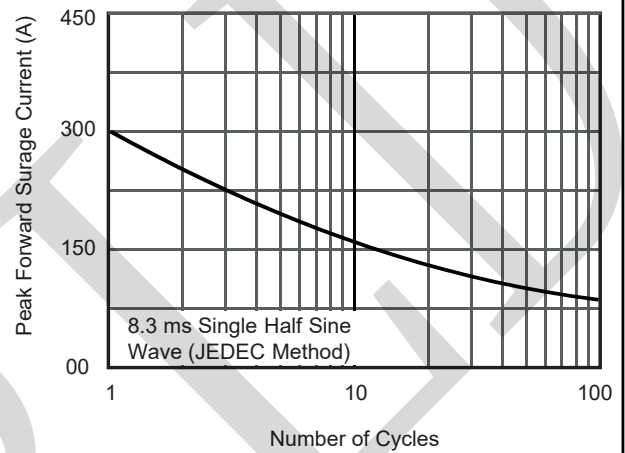


Fig.3 Typical Forward Voltage

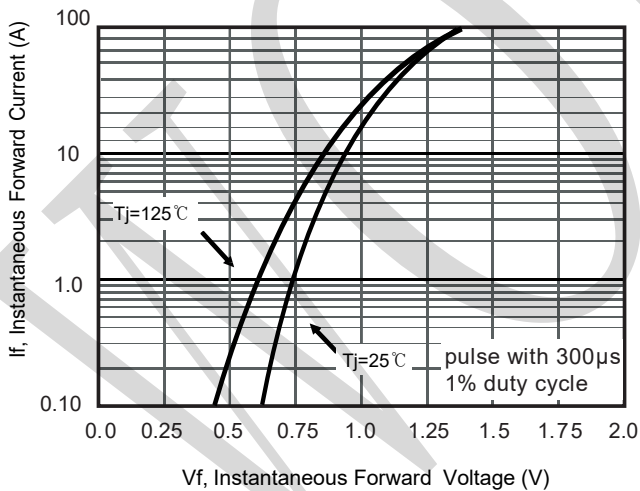
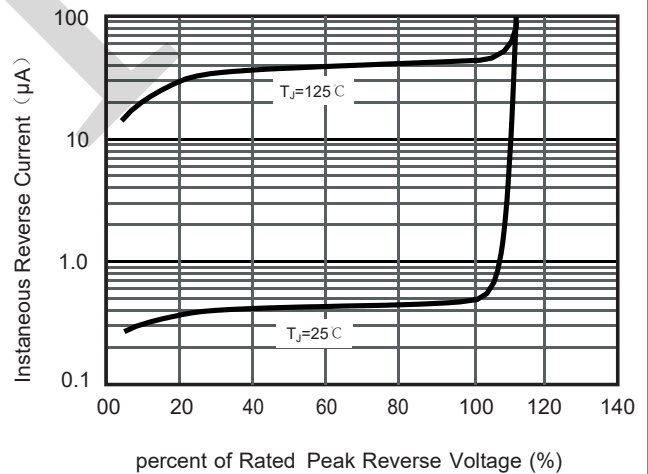
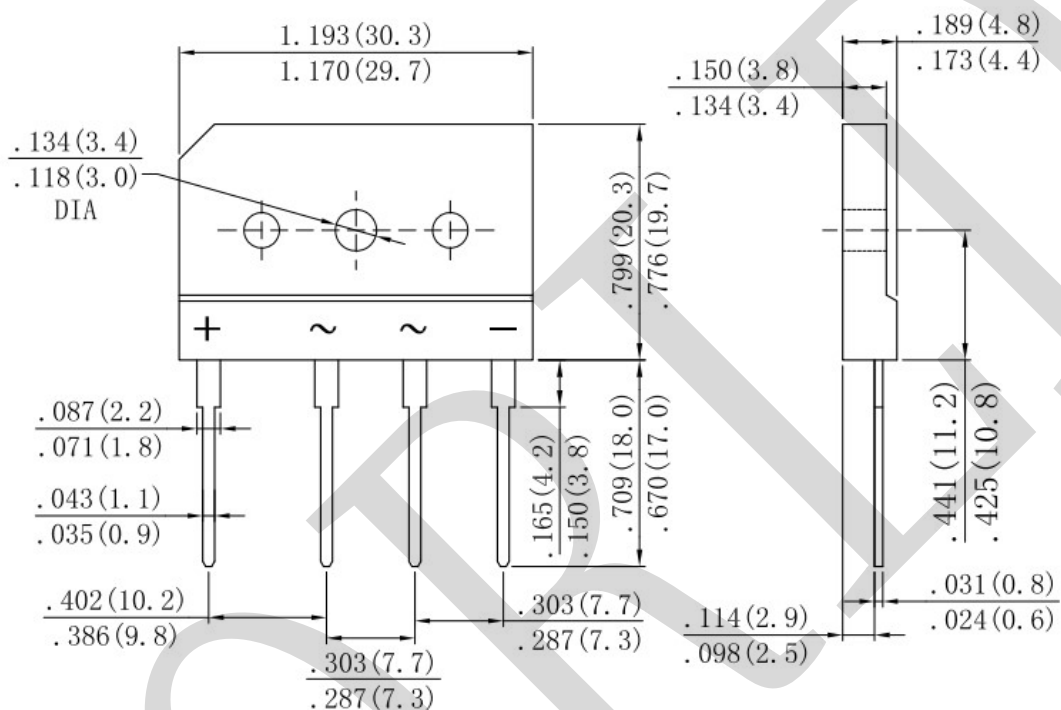


Fig.4 Typical Reverse Characteristics



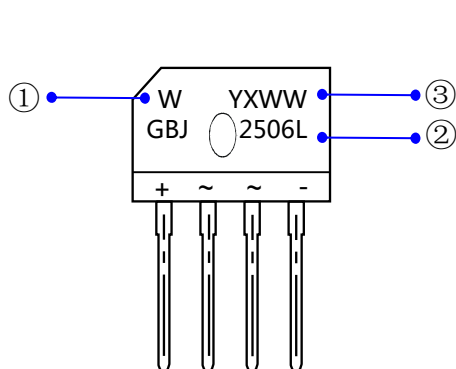
PACKAGE OUTLINE DIMENSIONS

Note: unit In(mm)



Dimensions in inches and (millimeters)

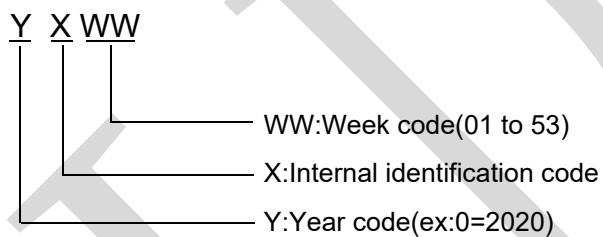
Marking Information



①W : Company's trademark

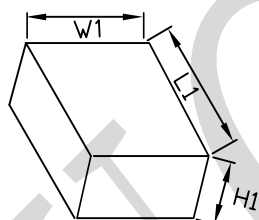
②Product model : GBJ2506L

③PDC information :

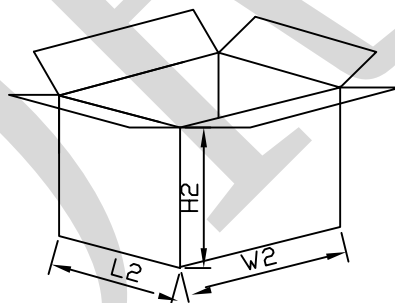


Packaging Information

1.Inside Box



2.Outside Box



Packaging Information

NO	UNIT	Inside Box			Outside Box		
		L1	W1	H1	L2	W2	H2
Size	mm	301	134	46	325	290	212
QTY	PCS	250PCS/carton			5,000PCS/carton,20boxes in total		
Note	Tolerance	≤20mm,±3mm; 21-100mm,±5mm; 101-500mm,±10mm					